

**ABSTRACT**

A method for removing a polysilicon layer from a non-silicon layer comprising the following steps. A structure having a non-silicon layer formed thereover is provided. A first polysilicon layer is formed upon the non-silicon layer. The first polysilicon layer is removed from over the non-silicon layer to expose the non-silicon layer using a  $\text{NH}_4\text{OH}$ :DIW dip solution process having a  $\text{NH}_4\text{OH}$ :DIW ratio of from about 1:2 to 1:8. Whereby the non-silicon layer is substantially unaffected by the  $\text{NH}_4\text{OH}$ :DIW dip solution process.